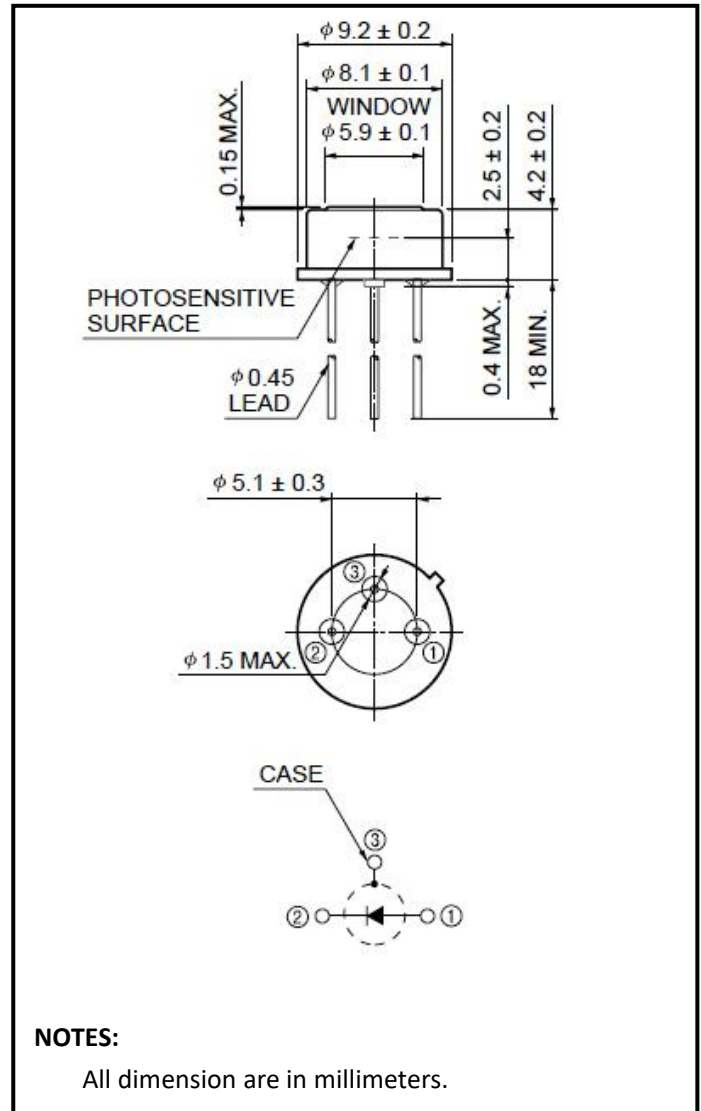


InGaAs PIN Photodiode

IGA3000



Description

OTRON SENSOR IGA3000 is a type of active area size of 3mm diameter active area IR sensitive detectors which exhibit excellent responsivity from 850nm to 1680nm, allowing high sensitivity to weak signals.

These large active area devices are ideal for use in infrared instrumentation and monitoring applications.

We can also custom type according to customer chip size or Package style enquiry.

Features

- * Low voltage operation
- * Isolated type are also available
- * Large Active Area Diameter
- * Spectral Range 850nm to 1700nm

General Ratings

- * Type InGaAs Photodiode
- * High linearity
- * Chip active area: $\phi 3.0$ mm
- * Low dark current

Applications

- * Optical Instrumentation
- * NIR Sensing
- * Laser Power Measurement
- * Power meters

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject change without notice

OTRON ELECTRONIC TECHNOLOGY CO.LTD

TEL:+86-21-54971821
FAX:+86-21-54971823

EMAL:frank.shuai@e-otron.com
<http://www.e-otron.com>

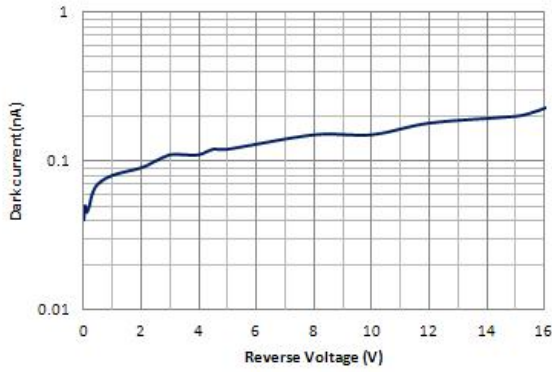


Absolute Maximum Ratings (Ta=25°C)

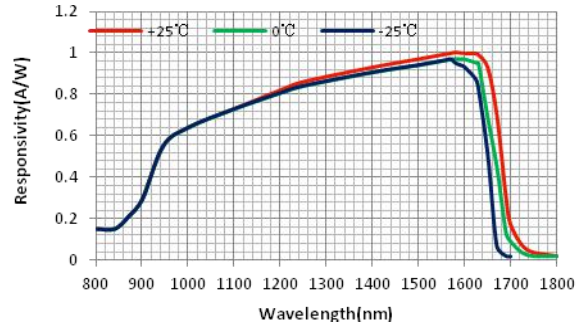
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Chip size	S	5.25*5.25				um
Active area	A	φ3000				um
Forward current	I _F	10				mA
Reverse current	I _R	10				mA
Dark current	I _D	V _R =0V		80		pA
		V _R =5V		40		nA
Rise time	t _R	V _R =5V;λ=850nm;R _L =50Ω		45		ns
Forward Voltage	V _F	I _F =1mA			0.5	V
Reverse breakdown voltage	V _{(BR)R}	I _R =10μA Ev=0lx	35	50		V
Junction Capacitance	C _J	V _R =0V f=1MHz		1900		pF
		V _R =5V f=1MHz		871		pF
Photo sensitivity	S _R	1310nm	0.90	0.95		A/W
		1550nm	0.95	1.10		
Spectral Application Range	λ _{range}		850		1680	nm
Spectral Response-Peak	λ _p			1600		nm
Shunt resistance	R _{sh}	V _R =10mV		0.1		GΩ
Saturation power	L	V _R =0V;λ=1.55μm		1		mW
		V _R =5V;λ=1.55μm		6		
Angular Resp 50% Resp Pt	θ _{1/2}			±55		Degrees
Noise Equivalent Power	NEP	V _R =5V λ=1550nm		5×10 ⁻¹⁴		W/Hz ^{1/2}
Specific Detectivity	D*	V _R =5V λ=1550nm		8.8×10 ¹²		cm(Hz/W) ^{1/2}

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject change without notice

■ Dark current vs. reverse voltage

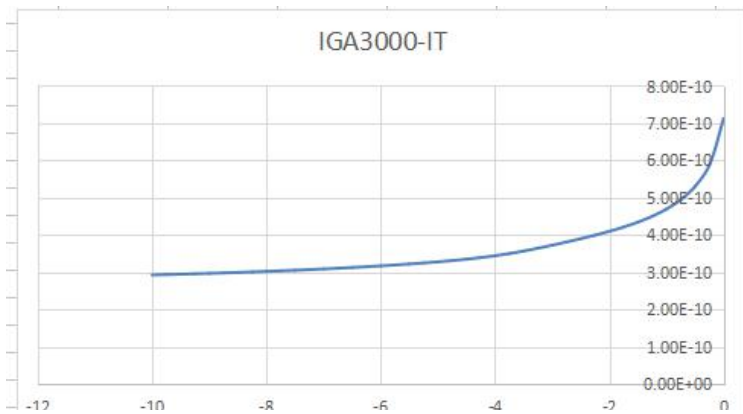


■ Spectral response



■ Relative Junction Capacitance

VS. Voltage



Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject change without notice

OTRON ELECTRONIC TECHNOLOGY CO.LTD

TEL:+86-21-54971821

FAX:+86-21-54971823

EMAL:frank.shuai@e-otron.com

<http://www.e-otron.com>